Freescale Semiconductor

MPX4250A Rev 7, 1/2009

Integrated Silicon Pressure Sensor Manifold Absolute Pressure Sensor On-Chip Signal Conditioned, Temperature Compensated and Calibrated

The MPX4250A series Manifold Absolute Pressure (MAP) sensor for engine control is designed to sense absolute air pressure within the intake manifold. This measurement can be used to compute the amount of fuel required for each cylinder.

The MPX4250A series piezoresistive transducer is a state-of-the-art monolithic silicon pressure sensor designed for a wide range of applications, particularly those employing a microcontroller or microprocessor with A/D inputs. This transducer combines advanced micromachining techniques, thin-film metallization and bipolar processing to provide an accurate, high-level analog output signal that is proportional to the applied pressure. The small form factor and high reliability of on-chip integration make the Freescale sensor a logical and economical choice for the automotive system engineer.

MPX4250A Series

20 to 250 kPa (2.9 to 36.3 psi) 0.2 to 4.9 V Output

Application Examples

- Turbo Boost Engine Control
- Ideally Suited for Microprocessor or Microcontroller-Based Systems

Features

- 1.5% Maximum Error Over 0° to 85°C
- Specifically Designed for Intake Manifold Absolute Pressure Sensing in Engine Control Systems
- · Patented Silicon Shear Stress Strain Gauge
- Temperature Compensated Over -40° to +125°C
- · Offers Reduction in Weight and Volume Compared to Existing Hybrid Modules
- Durable Epoxy Unibody Element or Thermoplastic Small Outline, Surface Mount Package
- Ideal for Non-Automotive Applications

ORDERING INFORMATION									
Device Name	Package	Case		# of Ports		Pressure Type			Davies Markins
Device Name	Options	No.	None	Single	Dual	Gauge	Differential	Absolute	Device Marking
Small Outline Packa	Small Outline Package (MPXA4250A Series)								
MPXA4250A6U	Rail	482	•					•	MPXA4250A
MPXA4250AC6U	Rail	482A		•				•	MPXA4250A
MPXA4250AC6T1	Tape and Reel	482A		•				•	MPXA4250A
Unibody Package (M	Jnibody Package (MPX4250A Series)								
MPX4250A	Tray	867	•					•	MPX4250A
MPX4250AP	Tray	867B		•				•	MPX4250A

SMALL OUTLINE PACKAGES



MPXA4250A6U CASE 482-01



MPXA4250AC6U/C6T1 CASE 482A-01



UNIBODY PACKAGES

MPX4250A CASE 867-08



MPX4250AP CASE 867B-04



Operating Characteristics

Table 1. Operating Characteristics ($V_S = 5.1 V_{DC}$, $T_A = 25^{\circ}C$ unless otherwise noted, P1 > P2, Decoupling circuit shown in Figure 3 required to meet electrical specifications.)

Characteristic	Symbol	Min	Тур	Max	Units	
Differential Pressure Range ⁽¹⁾		P _{OP}	20	_	250	kPa
Supply Voltage ⁽²⁾		V _S	4.85	5.1	5.35	V _{DC}
Supply Current		I _O	_	7.0	10	mAdc
Minimum Pressure Offset ⁽³⁾ @ V _S = 5.1 Volts	(0 to 85°C)	V _{OFF}	0.133	0.204	0.274	V _{DC}
Full Scale Output ⁽⁴⁾ @ V _S = 5.1 Volts	(0 to 85°C)	V _{FSO}	4.826	4.896	4.966	V _{DC}
Full Scale Span ⁽⁵⁾ @ V _S = 5.1 Volts	(0 to 85°C)	V _{FSS}	_	4.692	_	V _{DC}
Accuracy ⁽⁶⁾	(0 to 85°C)	_	_	_	±1.5	%V _{FSS}
Sensitivity		ΔV/ΔΡ	_	20	_	mV/kPa
Response Time ⁽⁷⁾		t _R	_	1.0	_	msec
Output Source Current at Full Scale Output		I _O +	_	0.1	_	mAdc
Warm-Up Time ⁽⁸⁾		_	_	20	_	msec
Offset Stability ⁽⁹⁾		_	_	±0.5	_	%V _{FSS}

- 1. 1.0 kPa (kiloPascal) equals 0.145 psi.
- 2. Device is ratiometric within this specified excitation range.
- 3. Offset (V_{OFF}) is defined as the output voltage at the minimum rated pressure.
- 4. Full Scale Output (V_{FSO}) is defined as the output voltage at the maximum or full rated pressure.
- 5. Full Scale Span (V_{FSS}) is defined as the algebraic difference between the output voltage at full rated pressure and the output voltage at the minimum rated pressure.
- 6. Accuracy (error budget) consists of the following:

Linearity: Output deviation at any temperature from a straight line relationship with pressure over the specified pressure

ange.

Temperature Hysteresis: Output deviation at any temperature within the operating temperature range, after the temperature is cycled to

and from the minimum or maximum operating temperature points, with zero differential pressure applied.

Pressure Hysteresis: Output deviation at any pressure within the specified range, when this pressure is cycled to and from the

minimum or maximum rated pressure, at 25°C.

TcSpan: Output deviation over the temperature range of 0° to 85°C, relative to 25°C.

TcOffset: Output deviation with minimum rated pressure applied, over the temperature range of 0° to 85°C, relative to 25°C.

Variation from Nominal: The variation from nominal values, for Offset or Full Scale Span, as a percent of VFSS, at 25°C.

- 7. Response Time is defined as the time form the incremental change in the output to go from 10% to 90% of its final value when subjected to a specified step change in pressure.
- 8. Warm-up Time is defined as the time required for the product to meet the specified output voltage after the pressure is stabilized.
- 9. Offset stability is the product's output deviation when subjected to 1000 hours of Pulsed Pressure, Temperature Cycling with Bias Test.

Maximum Ratings

Table 2. Maximum Ratings⁽¹⁾

Rating	Symbol	Value	Unit
Maximum Pressure ⁽²⁾ (P1 > P2)	P _{MAX}	1000	kPa
Storage Temperature	T _{STG}	-40 to +125	°C
Operating Temperature	T _A	-40 to +125	°C

- 1. TC = 25°C unless otherwise noted.
- 2. Exposure beyond the specified limits may cause permanent damage or degradation to the device.

Figure 1 shows a block diagram of the internal circuitry integrated on a pressure sensor chip.

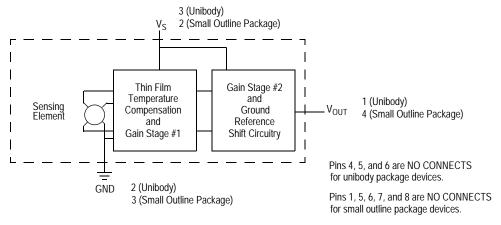


Figure 1. Fully Integrated Pressure Sensor Schematic for Unibody Package and Small Outline Package

On-chip Temperature Compensation and Calibration

Figure 2 illustrates the absolute pressure sensing chip in the basic chip carrier (Case 867). A fluorosilicone gel isolates the die surface and wire bonds from the environment, while allowing the pressure signal to be transmitted to the sensor diaphragm.

The MPX4250A series pressure sensor operating characteristics and internal reliability and qualification tests are based on use of dry air as the pressure media. Media, other than dry air, may have adverse effects on sensor performance and long-term reliability.

Contact the factory for information regarding media compatibility in your application.

Figure 3 shows the recommended decoupling circuit for interfacing the output of the integrated sensor to the A/D input of a microprocessor or microcontroller.

Figure 4 shows the sensor output signal relative to pressure input. Typical, minimum, and maximum output curves are shown for operation over temperature range of 0° to 85°C using the decoupling circuit shown in Figure 3. The output will saturate outside of the specified pressure range.

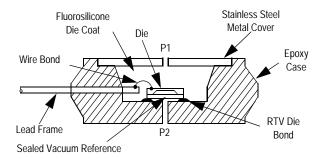


Figure 2. Cross Sectional Diagram (not to scale)

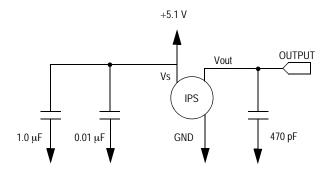


Figure 3. Recommended Power Supply Decoupling and Output Filtering (For additional output filtering, please refer to Application Note AN1646)

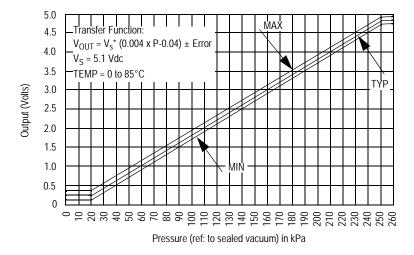


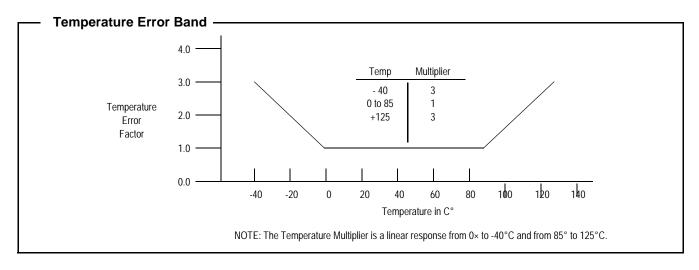
Figure 4. Output versus Absolute Pressure

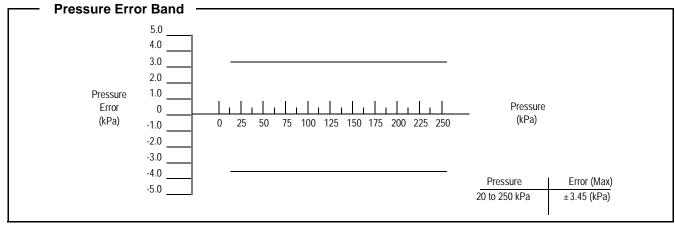
Transfer Function -

Nominal Transfer Value: $V_{OUT} = V_S (P \times 0.004 - 0.04)$

 \pm (Pressure Error \times Temp. Factor \times 0.004 \times V_S)

 $V_S = 5.1 \text{ V} \pm 0.25 \text{ V}_{DC}$





INFORMATION FOR USING THE SMALL OUTLINE PACKAGE (CASE 482)

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the surface mount packages must be the correct size to ensure proper solder connection interface between the board and the package. With the correct Footprint, the packages will self align when subjected to a

solder reflow process. It is always recommended to design boards with a solder mask layer to avoid bridging and shorting between solder pads.

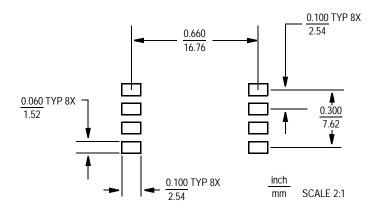
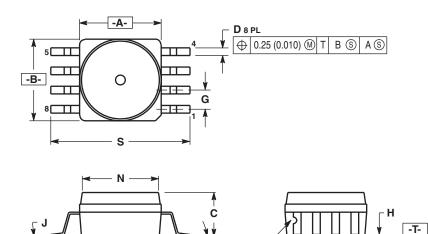


Figure 5. SOP Footprint (Case 482)

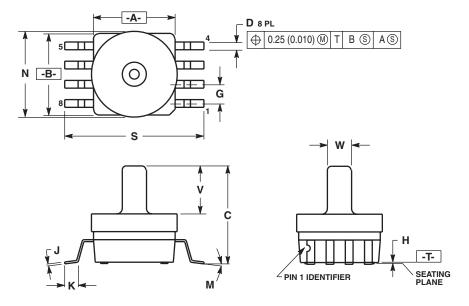


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006).
 5. ALL VERTICAL SURFACES 5' TYPICAL DRAFT.

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.415	0.425	10.54	10.79
В	0.415	0.425	10.54	10.79
С	0.212	0.230	5.38	5.84
D	0.038	0.042	0.96	1.07
G	0.100	BSC	2.54 BSC	
Н	0.002	0.010	0.05	0.25
J	0.009	0.011	0.23	0.28
K	0.061	0.071	1.55	1.80
M	0°	7°	0°	7°
N	0.405	0.415	10.29	10.54
S	0.709	0.725	18.01	18.41

CASE 482-01 ISSUE 0 SMALL OUTLINE PACKAGE

∠PIN 1 IDENTIFIER

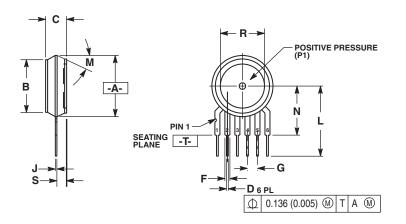


CASE 482A-01 ISSUE A SMALL OUTLINE PACKAGE

SEATING PLANE

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006).
 5. ALL VERTICAL SURFACES 5' TYPICAL DRAFT.

	INC	HES	MILLIM	ETERS		
DIM	MIN MAX		MIN	MAX		
Α	0.415	0.425	10.54	10.79		
В	0.415	0.425	10.54	10.79		
С	0.500	0.520	12.70	13.21		
D	0.038	0.042	0.96	1.07		
G	0.100	BSC	2.54	BSC		
Н	0.002	0.010	0.05	0.25		
J	0.009	0.011	0.23	0.28		
K	0.061	0.071	1.55	1.80		
M	0°	7°	0°	7°		
N	0.444	0.448	11.28	11.38		
S	0.709	0.725	18.01	18.41		
٧	0.245	0.255	6.22	6.48		
w	0.115	0.125	2.92	3.17		



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION -A- IS INCLUSIVE OF THE MOLD STOP RING. MOLD STOP RING NOT TO EXCEED 16.00 (0.630).

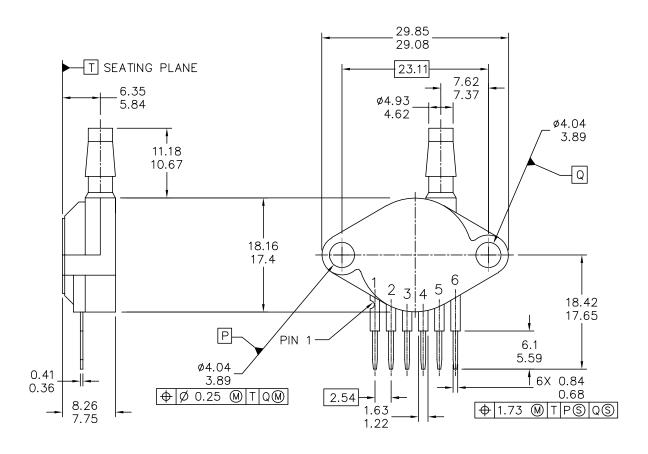
	INC	HES	MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.595	0.630	15.11	16.00	
В	0.514	0.534	13.06	13.56	
С	0.200	0.220	5.08	5.59	
D	0.027	0.033	0.68	0.84	
F	0.048	0.064	1.22	1.63	
G	0.100	BSC	2.54	2.54 BSC	
J	0.014	0.016	0.36	0.40	
L	0.695	0.725	17.65	18.42	
M	30° 1	MOV	30° N	MOM	
N	0.475	0.495	12.07	12.57	
R	0.430	0.450	10.92	11.43	
S	0.090	0.105	2.29	2.66	

STYLE 1:	
PIN 1.	VOUT
2.	GROUND
3.	VCC
4.	V1
5.	V2
6.	VEX

STYLE 2: PIN 1. OPEN 2. GROUND 3. -VOUT 4. VSUPPLY 5. +VOUT 6. OPEN

STYLE 3:
PIN 1. OPEN
2. GROUND
3. +VOUT
4. +VSUPPLY
5. -VOUT
6. OPEN

CASE 867-08 ISSUE N UNIBODY PACKAGE



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TITLE:	DOCUMENT NO: 98ASB42796B		REV: G	
SENSOR, 6 LEAD UNIBO	CASE NUMBER: 867B-04 28 JUL 2009			
AP & GP 01ASB09	STANDARD: NE	IN-JEDEC		

PAGE 1 OF 2

CASE 867B-04 ISSUE G UNIBODY PACKAGE

MPX4250A

NOTES:

- 1. DIMENSIONS ARE IN MILLIMETERS.
- 2. DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
- 3. 867B-01 THRU -3 OBSOLETE, NEW STANDARD 867B-04.

STYLE 1:

PIN 1: V OUT
2: GROUND
3: VCC
4: V1
5: V2
6: V EX

	MECHANICAL OUTLIN		PRINT VERSION NO	T TO SCALE	
TITLE:	DOCUMENT NO: 98ASB42796B		REV: G		
SENSOR, 6 LEAD UNIBOD	′	CASE NUMBER	R: 867B-04	28 JUL 2005	
AP & GP 01ASB090)8/B	STANDARD: NO	DN-JEDEC		

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CASE 867B-04 ISSUE G UNIBODY PACKAGE

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